

D¹ (b) cleaning the surface of said silicon wafer covered by said insulating film whose main surface is mainly formed of silicon dioxide, by a sheet-by-sheet manner with use of a processing solution containing hydrogen peroxide, hydricid fluoride salt, and water;

(c) removing said insulating film after said step (b) thereby to expose the silicon surface of said silicon wafer; and

(d) subjecting said silicon wafer to a heat-treatment after said step (c) thereby to form a gate oxide film over said silicon wafer.

Please add the following new claims to the application:

D² --31. A method of manufacturing a semiconductor integrated circuit device according to claim 17, wherein said processing solution etches the silicon oxide of the insulating film but does not etch the silicon wafer.

32. A method of manufacturing a semiconductor integrated circuit device according to claim 20, wherein said processing solution etches the silicon oxide of the insulating film but does not etch the silicon wafer.--
